

Low frequency transistor (−20V, −5A)

2SB1386 / 2SB1412

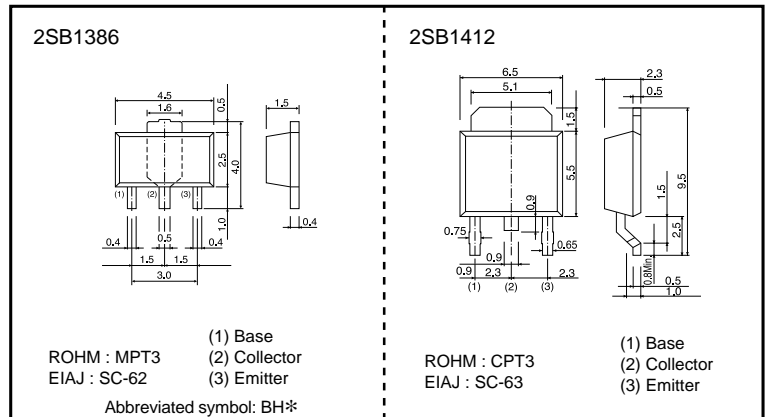
●Features

- 1) Low $V_{CE(sat)}$.
 $V_{CE(sat)} = -0.35V$ (Typ.)
 $(I_C/I_B = -4A / -0.1A)$
- 2) Excellent DC current gain characteristics.
- 3) Complements the 2SD2098 / 2SD2118.

●Structure

Epitaxial planar type
 PNP silicon transistor

●Dimensions (Unit : mm)



* Denotes h_{FE}

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-5	A(DC)
		-10	A(Pulse) *1
Collector power dissipation	2SB1386	0.5	W
		2	W *2
	2SB1412	1	W
		10	W(Tc=25°C)
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to 150	°C

*1 Single pulse, Pw=10ms

*2 When mounted on a 40×40×0.7 mm ceramic board.

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-30	-	-	V	I _C = -50μA
Collector-emitter breakdown voltage	BV _{CEO}	-20	-	-	V	I _C = -1mA
Emitter-base breakdown voltage	BV _{EB0}	-6	-	-	V	I _E = -50μA
Collector cutoff current	I _{CB0}	-	-	-0.5	μA	V _{CB} = -20V
Emitter cutoff current	I _{EBO}	-	-	-0.5	μA	V _{EB} = -5V
Collector-emitter saturation voltage	V _{CE(sat)}	-	0.35	-1.0	V	I _C /I _B = -4A/ -0.1A *
DC current transfer ratio	h _{FE}	82	-	390	-	V _{CE} = -2V, I _C = -0.5A *
Transition frequency	f _T	-	120	-	MHz	V _{CE} = -6V, I _E =50mA, f=100MHz
Output capacitance	C _{ob}	-	60	-	pF	V _{CB} = -20V, I _E =0A, f=1MHz

* Measured using pulse current.

●Packaging specifications and h_{FE}

Type	h _{FE}	Package	Taping	
		Code	T100	TL
		Basic ordering unit (pieces)	1000	2500
2SB1386	PQR	○	-	-
2SB1412	PQR	-	○	-

h_{FE} values are classified as follows :

Item	P	Q	R
h _{FE}	82 to 180	120 to 270	180 to 390

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●Electrical characteristic curves

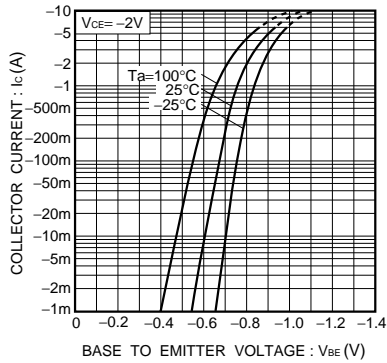


Fig.1 Grounded emitter propagation characteristics

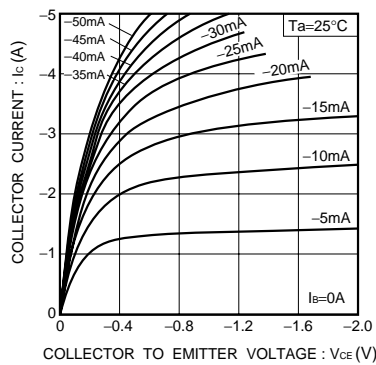


Fig.2 Grounded emitter output characteristics

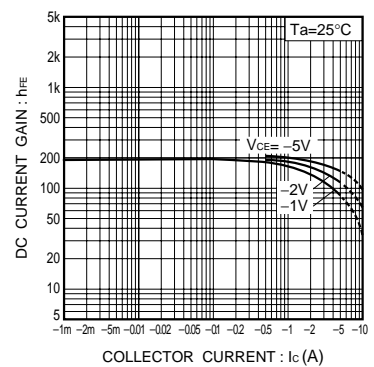


Fig.3 DC current gain vs. collector current (I)

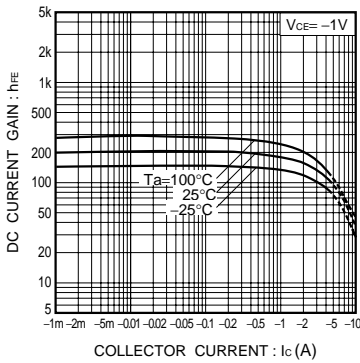


Fig.4 DC current gain vs. collector current (II)

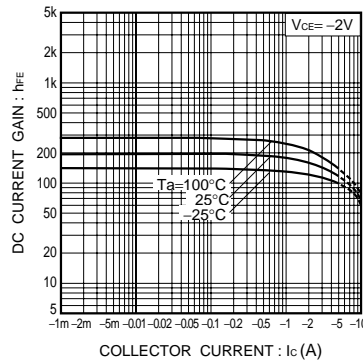


Fig.5 DC current gain vs. collector current (III)

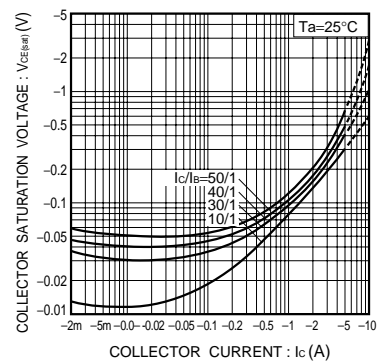


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

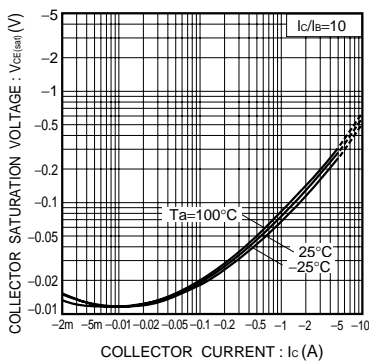


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

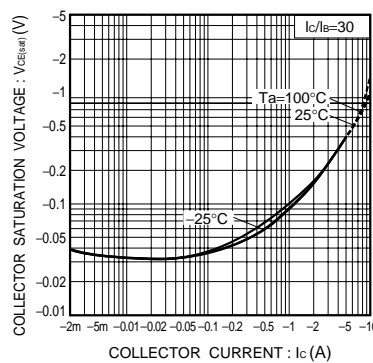


Fig.8 Collector-emitter saturation voltage vs. collector current (III)

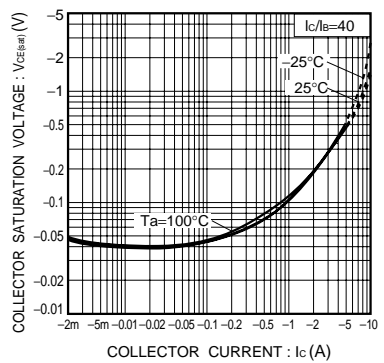


Fig.9 Collector-emitter saturation voltage vs. collector current (IV)

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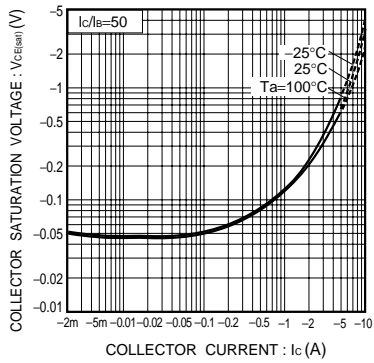


Fig.10 Collector-emitter saturation voltage vs. collector current (V)

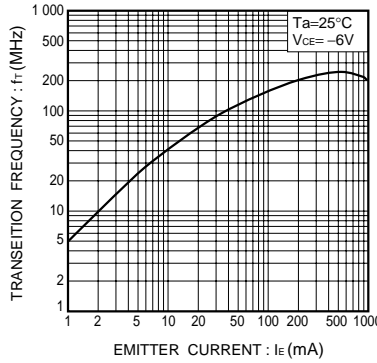


Fig.11 Gain bandwidth product vs. emitter current

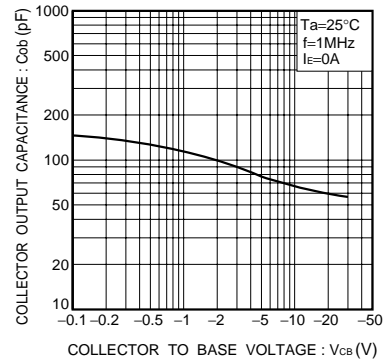


Fig.12 Collector output capacitance vs. collector-base voltage

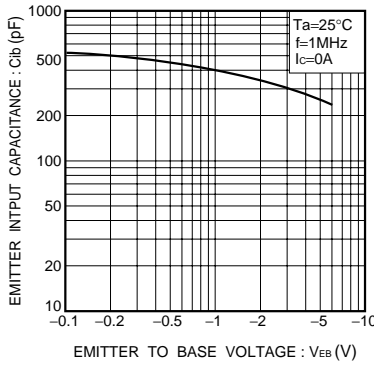


Fig.13 Emitter input capacitance vs. emitter-base voltage

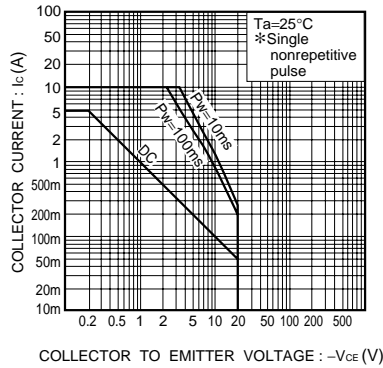


Fig.14 Safe operation area (2SB1412)

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